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(54) Title: PHOTODIODE DETECTOR AND METHOD OF FABRICATING THE SAME

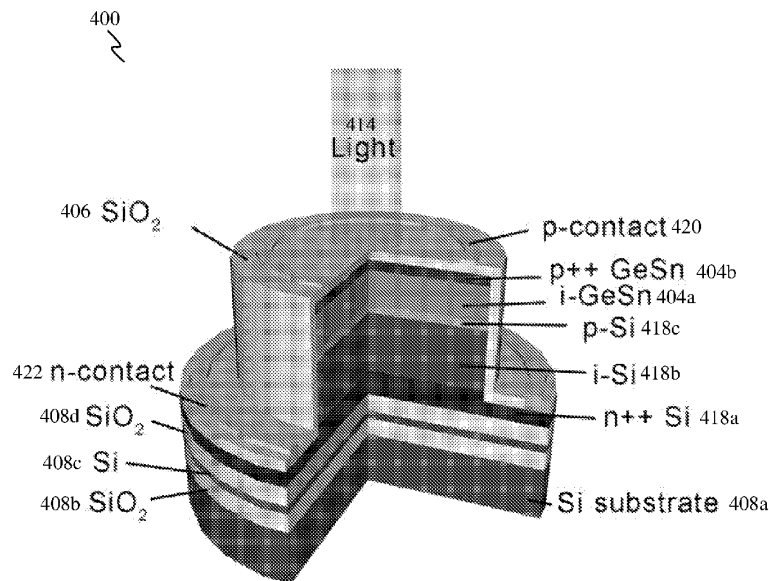


FIG. 4

(57) Abstract: According to embodiments of the present invention, a photodiode detector is provided. The photodiode detector includes an optical cavity including an overlying light-receiving portion and an underlying mirror; and a GeSn absorption layer. The GeSn absorption layer may be disposed within the optical cavity and arranged between the overlying light-receiving portion and the underlying mirror. The overlying light-receiving portion may be configured to receive light to be detected by the photodiode detector. According to further embodiments of the present invention, a method of fabricating a photodiode detector is also provided.

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